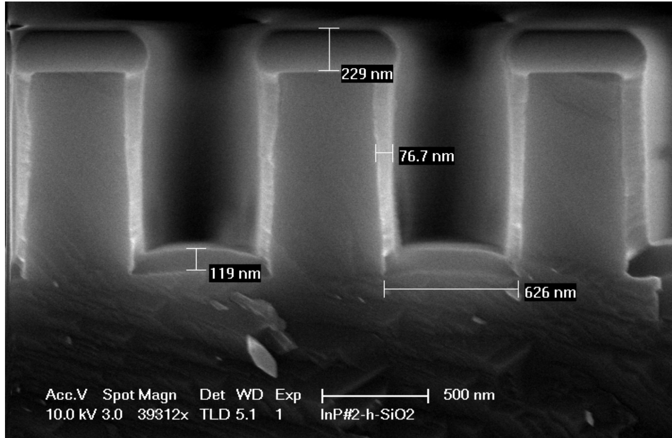
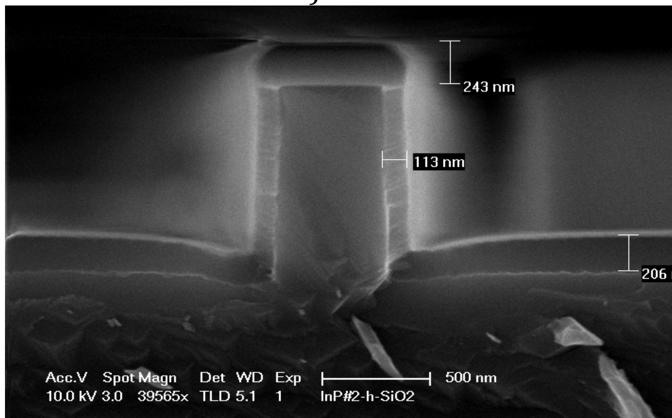
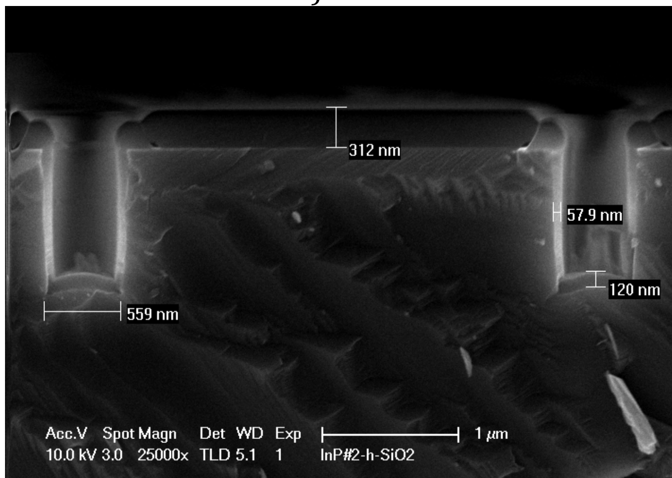


a)



b)



c)

Figure 3 (a) (in a closed trench area), **(b)** (in an open area), and **(c)**. Sidewall coverage of SiO_2 film, deposited using Unaxis ICP tool (PM3) at 100 ^{o}C, with the chamber pressure=15 mT, bias/ICP powers=5/400 W, 2%SiH_4 (diluted in He)/O_2/Ar=250/10/20 sccm, and deposition time=383 s [Sample's solvent clean and BHF dip (two minutes, to remove the remaining SiO2 etch mask) were applied prior to the deposition].